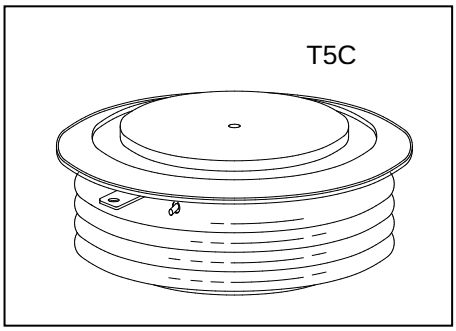
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Device Type	V_{RRM} (1)	V_{DRM} (1)	V_{RSM} (1)
KP750/20	2000	2000	2200
KP750/22	2200	2200	2400
KP750/24	2400	2400	2500

V_{RRM} = Repetitive peak reverse voltage
V_{DRM} = Repetitive peak off state voltage
V_{RSM} = Non repetitive peak reverse voltage (2)

Repetitive peak reverse leakage and off state leakage	I_{RRM}/I_{DRM}	2 mA 45 mA (3)
Critical rate of voltage rise	dv/dt (4)	1000 V/μs

Notes:
(1) All voltage ratings are specified for an applied 50Hz sinusoidal waveform over the temperature range -40 °C to +125 °C.
(2) 10 msec. max. pulse width
(3) Maximum value for Tj = 125 °C.
(4) Minimum value for linear and exponential waveshape to 67% rated V_{DRM}. Gate open. Tj = 125 °C.
(5).The value of di/dt is established in accordance with EIA/NIMA Standard JB/T 8950.2-2013

Average value of on-state current	$I_{T(AV)}$		750		A	Sinewave,180° conduction,T_c=70°C
RMS value of on-state current	I_{TRMS}		1178		A	Nominal value
Peak one cycle surge (non repetitive) current	I_{TSM}		12000		A	10.0 msec (50Hz), sinusoidal wave-shape, 180° conduction, T_j = 125 °C
I square t	I^2t		$7.2x10^5$		A^2s	10 msec
Latching current	I_L		1000		mA	V_D = 12 V; R_L= 12 ohms
Holding current	I_H		200		mA	V_D = 12 V; I = 2.5 A
Peak on-state voltage	V_{TM}		1.8		V	I_{TM}=1500A;Tj =25°C
Threshold voltage, low-level	V_{TO}		0.95		V	Tj=125°C
Slope resistance, low-level	r_T		0.5		mΩ	800A to 2300A
Critical rate of rise of on-state current(5)	di/dt		100		A/μs	Tj=125°C; V_D = 0.67 V_{DRM}; f=50Hz; I_{TM}=1000A

